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I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

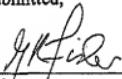
Customer Number: 76681

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008


Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)

MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in *U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A*.

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to *MEMC Electronic Materials, Inc.* via Assignment(s) recorded with the United States Patent and Trademark Office at the *Reel/Frame Numbers on the attached Schedule A*.

The undersigned, *Dr. Graham Fisher, Director of Intellectual Property*, has full authorization to act on behalf of Assignee *MEMC Electronic Materials, Inc.*

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. & FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2358.4	5961	US-2002-0043206 A1 4/18/2002	10/008,812	6,728,764 4/27/2004	MEMC Electronic Materials, Inc.	Continuation of 09/485,563 recorded at 01/1380/0967	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS
MEMC2385	6059		09/287,916	6,241,818 6/5/2001	MEMC Electronic Materials, Inc.	09/592/2403/30	METHOD AND SYSTEM OF CONTROLLING TAPER GROWTH IN A SEMICONDUCTOR CRYSTAL GROWTH PROCESS
MEMC2396	6222		09/286,982 3/16/1999	6,214,109 4/10/2001	MEMC Electronic Materials, Inc.	Division of 09/7732,527 recorded at 00/286/0756	APPARATUS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC
MEMC2410	2416		09/270,366 3/16/1999	6,376,842 4/30/2002	MEMC Electronic Materials, Inc.	01/028/7/0032	VACANCY DOMINATED, DEFECT-FREE SILICON
MEMC2410.1	3844	US 2002-0073480-A1 6/27/2002	10/006,545 10/24/2001	6,846,997 1/11/2005	MEMC Electronic Materials, Inc.	Division of 09/277,938 recorded at 01/028/7/0032	VACANCY DOMINATED, DEFECT-FREE SILICON
287446251 (MEMC2410.3)	7718	US2005-0233906 A1 10/27/2005	11/10/241 4/8/2005	MEMC Electronic Materials, Inc.	Continuation of 10/119,139 which is a continuation of 10/000,545 recorded at 01/028/7/0032	VACANCY-DOMINATED, DEFECT-FREE SILICON	
MEMC2442.1	1380		09/666,622 9/14/2000	6,391,662 5/21/2002	MEMC Electronic Materials, Inc.	01/129/0/0576	PROCESS FOR DETECTING AGGLOMERATED INTRINSIC POINT DEFECTS BY METAL DECORATION
MEMC2443.1	1384		09/656,421 9/14/2000	6,532,537 5/21/2003	MEMC Electronic Materials, Inc.	01/131/0/126	METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS
2874472 (MEMC2444.3)	4026	US2008-0196587 A1 10/23/2003	10/430,463 6/6/2003	MEMC Electronic Materials, Inc.	09/851,145 recorded at 01/132/0/058	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	
MEMC2443.2	7412		09/807,907 6/8/2001	6,520,191 2/18/2003	MEMC Electronic Materials, Inc.	01/169/2/319	CARRIER FOR CLEANING SILICON WAFERS
MEMC2453	8592	US-2001-0003268-A1 6/14/2001	09/344,038 6/25/1999	6,314,516 1/16/2001	MEMC Electronic Materials, Inc.	01/038/1/004	PROCESS FOR PREPARING DEFECT-FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS
MEMC2458.1	7076	US-2001-0227743-A1 10/11/2001	09/856,232 6/1/2001	6,506,255 12/31/2002	MEMC Electronic Materials, Inc.	Continuation of 09/544,036 recorded at 01/048/1/004	PROCESS FOR GROWING SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS WHILE SUPPRESSING THE FORMATION OF AGGLOMERATED INTRINSIC POINT DEFECTS